
HM62V16258B Series

4 M SRAM (256-kword × 16-bit)

HITACHI

ADE-203-975B (Z)

Rev. 2.0

Oct. 14, 1999

Description

The Hitachi HM62V16258B Series is 4-Mbit static RAM organized 262,144-word × 16-bit. HM62V16258B Series has realized higher density, higher performance and low power consumption by employing Hi-CMOS process technology. It offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It is packaged in standard 44-pin plastic TSOPII.

Features

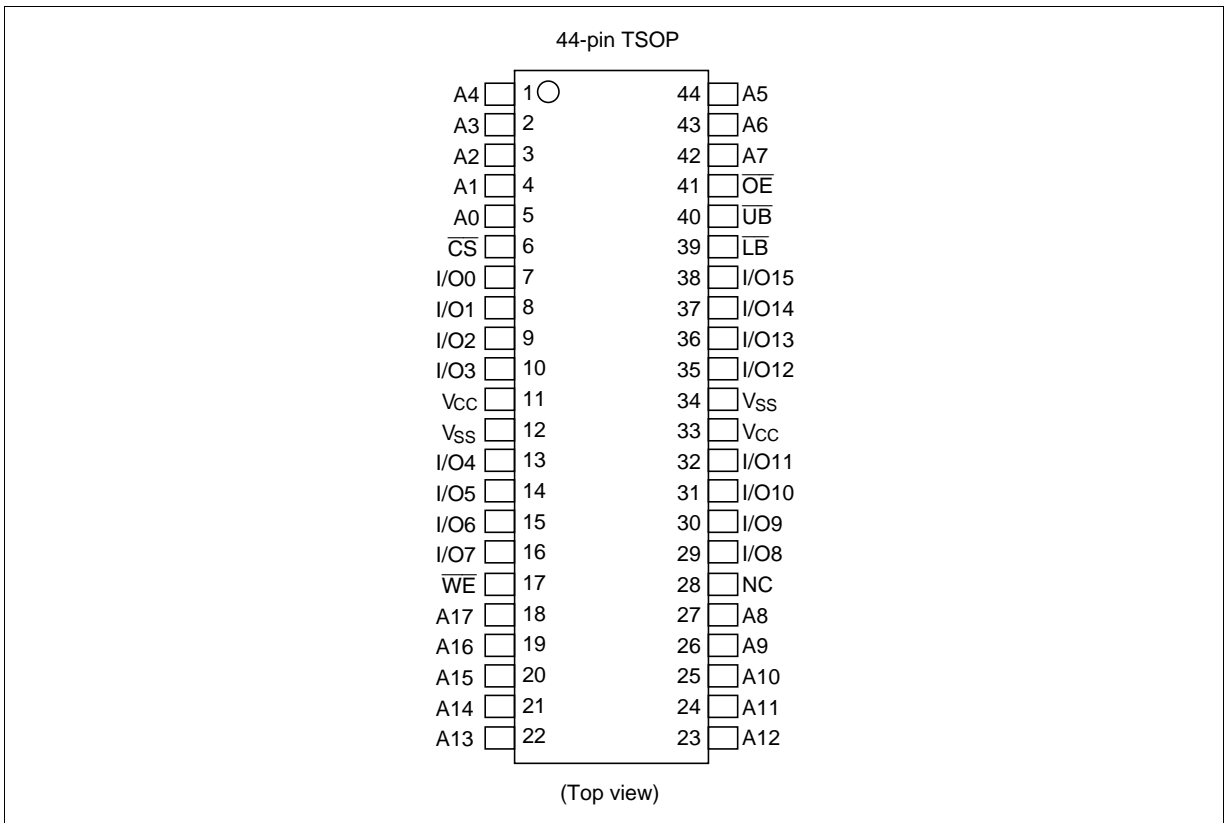
- Single 3.0 V supply: 2.7 V to 3.6 V
- Fast access time: 70 ns/85 ns (max)
- Power dissipation:
 - Active: 9 mW (typ)
 - Standby: 3 μW (typ)
- Completely static memory.
 - No clock or timing strobe required
- Equal access and cycle times
- Common data input and output.
 - Three state output
- Battery backup operation.

HM62V16258B Series

Ordering Information

Type No.	Access time	Package
HM62V16258BLTT-7	70 ns	400-mil 44-pin plastic TSOPII (normal-bend type) (TTP-44DB)
HM62V16258BLTT-8	85 ns	
HM62V16258BLTT-7SL	70 ns	
HM62V16258BLTT-8SL	85 ns	

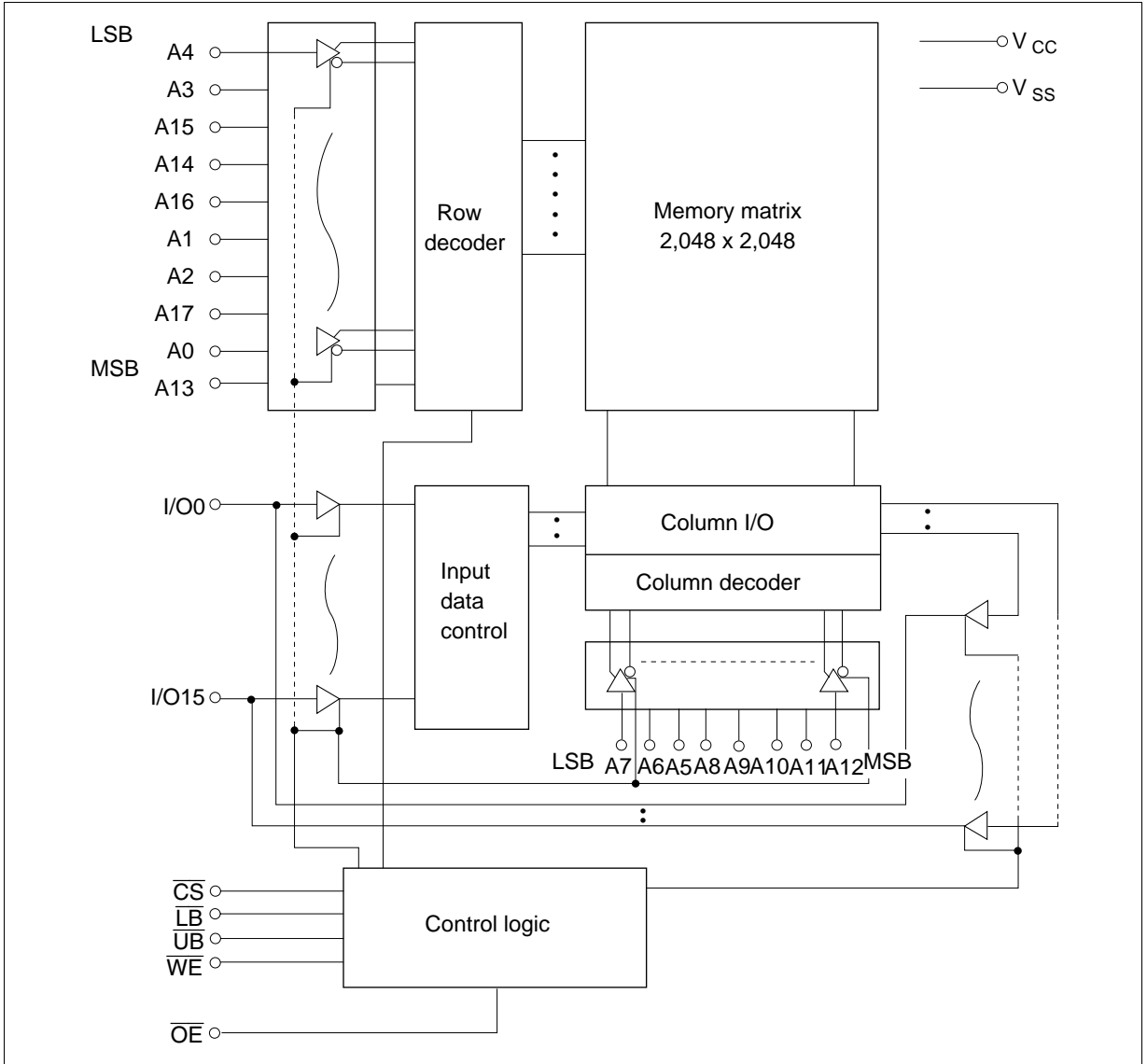
Pin Arrangement



Pin Description

Pin name	Function
A0 to A17	Address input
I/O0 to I/O15	Data input/output
\overline{CS}	Chip select
\overline{WE}	Write enable
\overline{OE}	Output enable
\overline{LB}	Lower byte select
\overline{UB}	Upper byte select
V _{CC}	Power supply
V _{SS}	Ground
NC	No connection

Block Diagram



Operation Table

\overline{CS}	\overline{WE}	\overline{OE}	\overline{UB}	\overline{LB}	I/O0 to I/O7	I/O8 to I/O15	Operation
H	×	×	×	×	High-Z	High-Z	Standby
×	×	×	H	H	High-Z	High-Z	Standby
L	H	L	L	L	Dout	Dout	Read
L	H	L	H	L	Dout	High-Z	Lower byte read
L	H	L	L	H	High-Z	Dout	Upper byte read
L	L	×	L	L	Din	Din	Write
L	L	×	H	L	Din	High-Z	Lower byte write
L	L	×	L	H	High-Z	Din	Upper byte write
L	H	H	×	×	High-Z	High-Z	Output disable

Note: H: V_{IH} , L: V_{IL} , ×: V_{IH} or V_{IL}

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage relative to V_{SS}	V_{CC}	-0.5 to +4.6	V
Terminal voltage on any pin relative to V_{SS}	V_T	-0.5*1 to $V_{CC} + 0.3$ *2	V
Power dissipation	P_T	1.0	W
Storage temperature range	Tstg	-55 to +125	°C
Storage temperature range under bias	Tbias	-10 to +85	°C

Notes: 1. V_T min: -3.0 V for pulse half-width ≤ 30 ns.

2. Maximum voltage is +4.6 V.

DC Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply voltage	V_{CC}	2.7	3.0	3.6	V	
	V_{SS}	0	0	0	V	
Input high voltage	V_{IH}	2.0	—	$V_{CC} + 0.3$	V	
Input low voltage	V_{IL}	-0.3	—	0.6	V	1
Ambient temperature range	T_a	0	—	70	°C	

Note: 1. V_{IL} min: -3.0 V for pulse half-width ≤ 30 ns.

DC Characteristics

Parameter	Symbol	Min	Typ* ¹	Max	Unit	Test conditions	
Input leakage current	$ I_{LI} $	—	—	1	μA	$V_{in} = V_{SS}$ to V_{CC}	
Output leakage current	$ I_{LO} $	—	—	1	μA	$\overline{CS} = V_{IH}$ or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$ or, $\overline{LB} = \overline{UB} = V_{IH}$, $V_{IO} = V_{SS}$ to V_{CC}	
Operating current	I_{CC}	—	—	20	mA	$\overline{CS} = V_{IL}$, Others = V_{IH}/V_{IL} , $I_{IO} = 0 \text{ mA}$	
Average operating current	HM62V16258B-7	I_{CC1}	—	—	70	mA	Min. cycle, duty = 100%, $I_{IO} = 0 \text{ mA}$, $\overline{CS} = V_{IL}$, Others = V_{IH}/V_{IL}
	HM62V16258B-8	I_{CC1}	—	—	65	mA	
		I_{CC2}	—	3	15	mA	Cycle time = 1 μs , duty = 100%, $I_{IO} = 0 \text{ mA}$, $\overline{CS} \leq 0.2 \text{ V}$, $V_{IH} \geq V_{CC} - 0.2 \text{ V}$, $V_{IL} \leq 0.2 \text{ V}$
Standby current	I_{SB}	—	—	0.3	mA	$\overline{CS} = V_{IH}$	
Standby current	I_{SB1}^{*2}	—	1	40	μA	$0 \text{ V} \leq V_{in}$ $\overline{CS} \geq V_{CC} - 0.2 \text{ V}$	
		I_{SB1}^{*3}	—	1	20	μA	
Output high voltage	V_{OH}	2.4	—	—	V	$I_{OH} = -1 \text{ mA}$	
		$V_{CC} - 0.2$	—	—	V	$I_{OH} = -100 \mu\text{A}$	
Output low voltage	V_{OL}	—	—	0.4	V	$I_{OL} = 2 \text{ mA}$	
		—	—	0.2	V	$I_{OL} = 100 \mu\text{A}$	

Notes: 1. Typical values are at $V_{CC} = 3.0 \text{ V}$, $T_a = +25^\circ\text{C}$ and not guaranteed.

2. This characteristic is guaranteed only for L version.

3. This characteristic is guaranteed only for L-SL version.

Capacitance ($T_a = +25^\circ\text{C}$, $f = 1.0 \text{ MHz}$)

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	Note
Input capacitance	C_{in}	—	—	8	pF	$V_{in} = 0 \text{ V}$	1
Input/output capacitance	C_{IO}	—	—	10	pF	$V_{IO} = 0 \text{ V}$	1

Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics (Ta = 0 to +70°C, V_{CC} = 2.7 V to 3.6 V, unless otherwise noted.)

Test Conditions

- Input pulse levels: V_{IL} = 0.4 V, V_{IH} = 2.2 V
- Input rise and fall time: 5 ns
- Input timing reference levels: 1.4 V
- Output timing reference levels: 1.4 V
- Output load: 1 TTL + 30 pF (HM62V16258B-7) (Including scope and jig)
1 TTL + 100 pF (HM62V16258B-8) (Including scope and jig)

Read Cycle

Parameter	Symbol	HM62V16258B				Unit	Notes
		-7		-8			
		Min	Max	Min	Max		
Read cycle time	t _{RC}	70	—	85	—	ns	
Address access time	t _{AA}	—	70	—	85	ns	
Chip select access time	t _{ACS}	—	70	—	85	ns	
Output enable to output valid	t _{OE}	—	40	—	45	ns	
Output hold from address change	t _{OH}	10	—	10	—	ns	
$\overline{\text{LB}}$, $\overline{\text{UB}}$ access time	t _{BA}	—	70	—	85	ns	
Chip select to output in low-Z	t _{CLZ}	10	—	10	—	ns	2, 3
$\overline{\text{LB}}$, $\overline{\text{UB}}$ enable to low-z	t _{BLZ}	5	—	5	—	ns	2, 3
Output enable to output in low-Z	t _{OLZ}	5	—	5	—	ns	2, 3
Chip deselect to output in high-Z	t _{CHZ}	0	25	0	25	ns	1, 2, 3
$\overline{\text{LB}}$, $\overline{\text{UB}}$ disable to high-Z	t _{BHZ}	0	25	0	25	ns	1, 2, 3
Output disable to output in high-Z	t _{OHZ}	0	25	0	25	ns	1, 2, 3

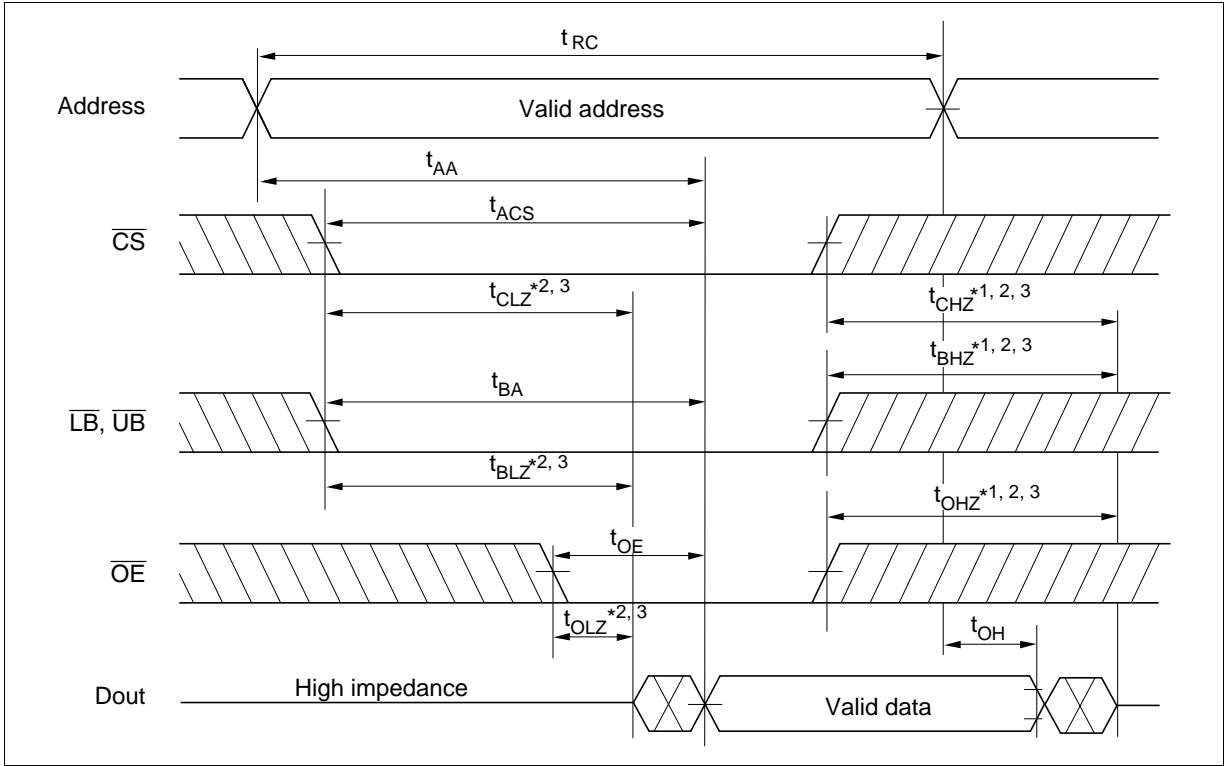
Write Cycle

Parameter	Symbol	HM62V16258B				Unit	Notes
		-7		-8			
		Min	Max	Min	Max		
Write cycle time	t_{WC}	70	—	85	—	ns	
Address valid to end of write	t_{AW}	60	—	70	—	ns	
Chip selection to end of write	t_{CW}	60	—	70	—	ns	5
Write pulse width	t_{WP}	50	—	55	—	ns	4
\overline{LB} , \overline{UB} valid to end of write	t_{BW}	55	—	70	—	ns	
Address setup time	t_{AS}	0	—	0	—	ns	6
Write recovery time	t_{WR}	0	—	0	—	ns	7
Data to write time overlap	t_{DW}	30	—	35	—	ns	
Data hold from write time	t_{DH}	0	—	0	—	ns	
Output active from end of write	t_{OW}	5	—	5	—	ns	2
Output disable to output in High-Z	t_{OHZ}	0	25	0	25	ns	1, 2
Write to output in high-Z	t_{WHZ}	0	25	0	25	ns	1, 2

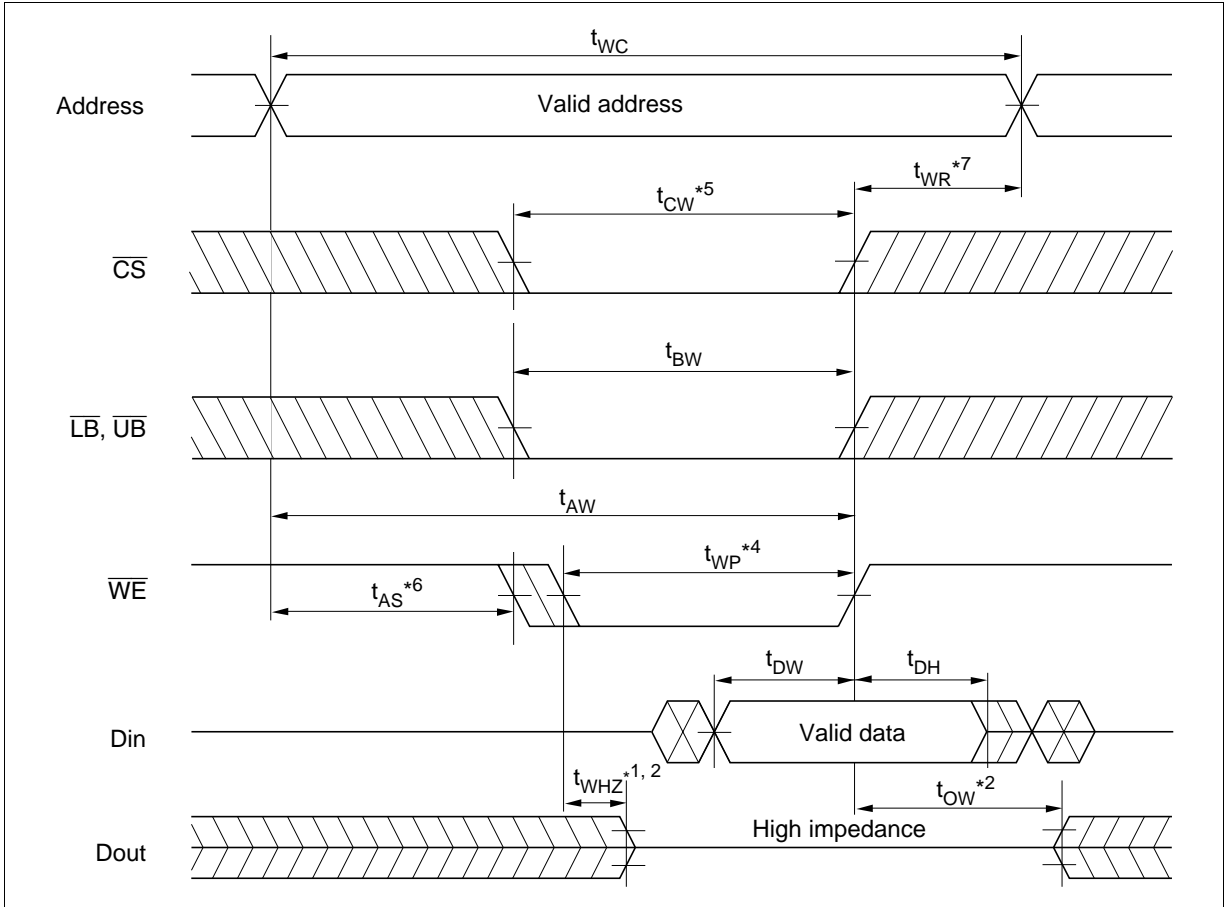
- Notes:
- t_{CHZ} , t_{OHZ} , t_{WHZ} and t_{BHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
 - This parameter is sampled and not 100% tested.
 - At any given temperature and voltage condition, t_{HZ} max is less than t_{LZ} min both for a given device and from device to device.
 - A write occurs during the overlap of a low \overline{CS} , a low \overline{WE} and a low \overline{LB} or a low \overline{UB} . A write begins at the latest transition among \overline{CS} going low, \overline{WE} going low and \overline{LB} going low or \overline{UB} going low. A write ends at the earliest transition among \overline{CS} going high, \overline{WE} going high and \overline{LB} going high or \overline{UB} going high. t_{WP} is measured from the beginning of write to the end of write.
 - t_{CW} is measured from the later of \overline{CS} going low to the end of write.
 - t_{AS} is measured from the address valid to the beginning of write.
 - t_{WR} is measured from the earliest of \overline{CS} or \overline{WE} going high to the end of write cycle.

Timing Waveform

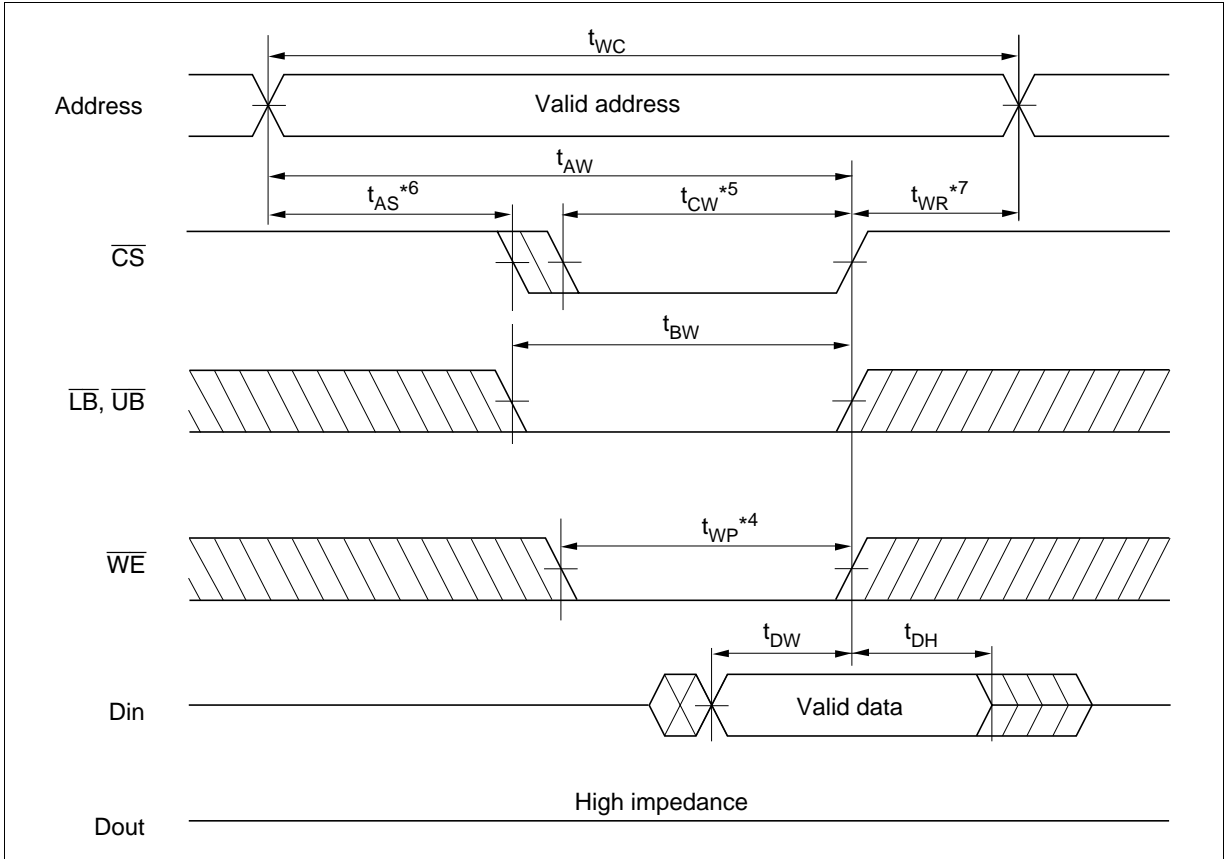
Read Cycle



Write Cycle (1) ($\overline{\text{WE}}$ Clock)

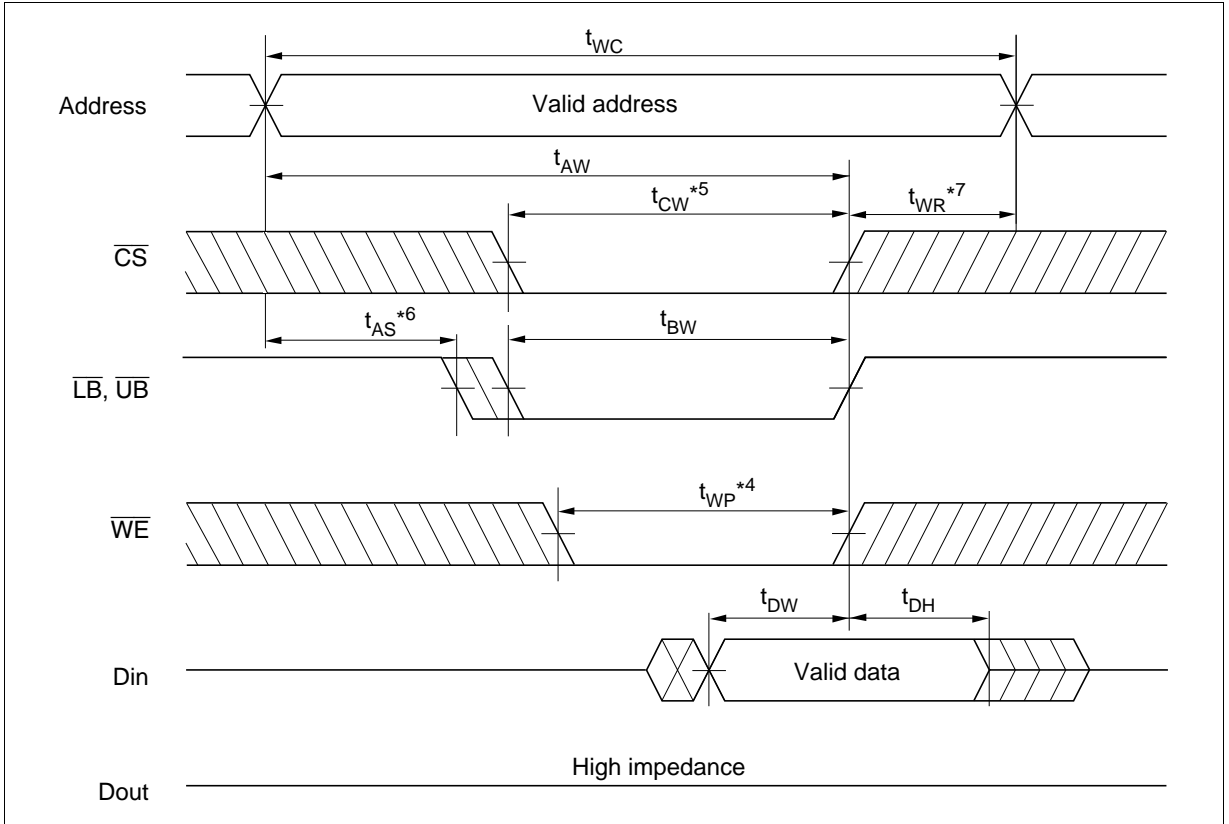


Write Cycle (2) ($\overline{\text{CS}}$ Clock, $\overline{\text{OE}} = V_{\text{IH}}$)



HM62V16258B Series

Write Cycle (3) ($\overline{\text{LB}}$, $\overline{\text{UB}}$ Clock, $\overline{\text{OE}} = V_{\text{IH}}$)

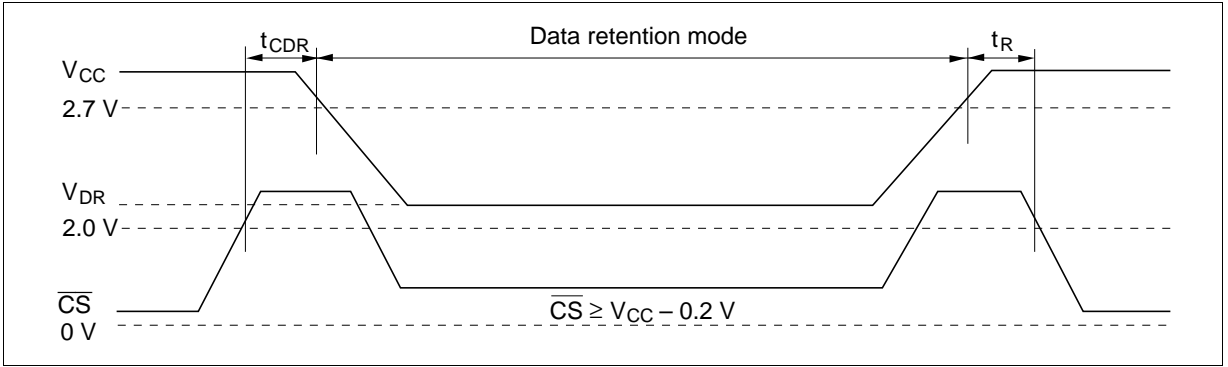


Low V_{CC} Data Retention Characteristics ($T_a = 0$ to $+70^\circ\text{C}$)

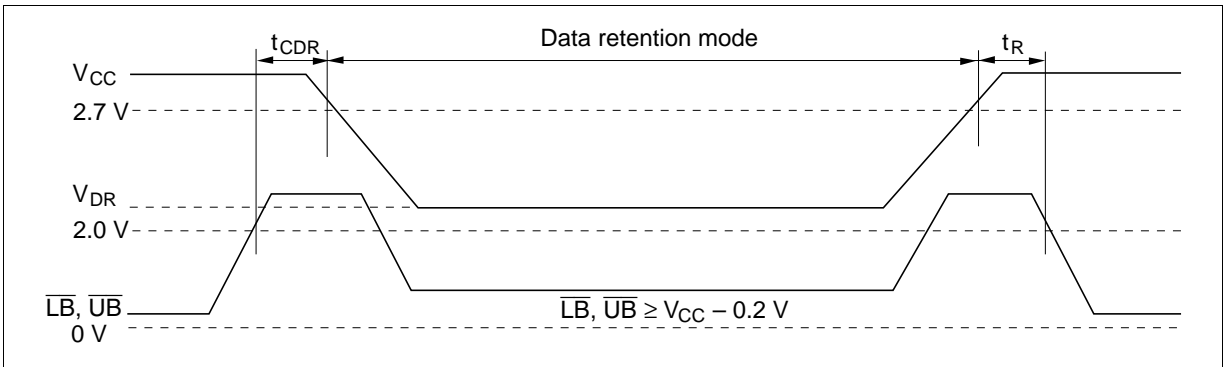
Parameter	Symbol	Min	Typ* ⁴	Max	Unit	Test conditions* ³
V_{CC} for data retention	V_{DR}	2.0	—	—	V	$V_{in} \geq 0\text{V}$ (1) $\overline{CS} \geq V_{CC} - 0.2\text{V}$ or (2) $\overline{LB} = \overline{UB} \geq V_{CC} - 0.2\text{V}$ $\overline{CS} \leq 0.2\text{V}$
Data retention current	I_{CCDR}^{*1}	—	0.8	20	μA	$V_{CC} = 3.0\text{V}$, $V_{in} \geq 0\text{V}$ (1) $\overline{CS} \geq V_{CC} - 0.2\text{V}$ or (2) $\overline{LB} = \overline{UB} \geq V_{CC} - 0.2\text{V}$ $\overline{CS} \leq 0.2\text{V}$
	I_{CCDR}^{*2}	—	0.8	10	μA	
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	See retention waveform
Operation recovery time	t_R	t_{RC}^{*5}	—	—	ns	

- Notes:
1. This characteristic is guaranteed only for L-version, 10 μA max. at $T_a = 0$ to $+40^\circ\text{C}$.
 2. This characteristic is guaranteed only for L-SL version, 5 μA max. at $T_a = 0$ to $+40^\circ\text{C}$.
 3. \overline{CS} controls address buffer, \overline{WE} buffer, \overline{OE} buffer, \overline{LB} , \overline{UB} buffer and Din buffer. If \overline{CS} controls data retention mode, V_{in} levels (address, \overline{WE} , \overline{OE} , \overline{LB} , \overline{UB} , I/O) can be in the high impedance state. If \overline{LB} , \overline{UB} controls data retention mode, \overline{LB} , \overline{UB} must be $\overline{LB} = \overline{UB} \geq V_{CC} - 0.2\text{V}$, \overline{CS} must be $\overline{CS} \leq 0.2\text{V}$. The other input levels (address, \overline{WE} , \overline{OE} , I/O) can be in the high impedance state.
 4. Typical values are at $V_{CC} = 3.0\text{V}$, $T_a = +25^\circ\text{C}$ and not guaranteed.
 5. t_{RC} = read cycle time.

Low V_{CC} Data Retention Timing Waveform (1) (\overline{CS} Controlled)



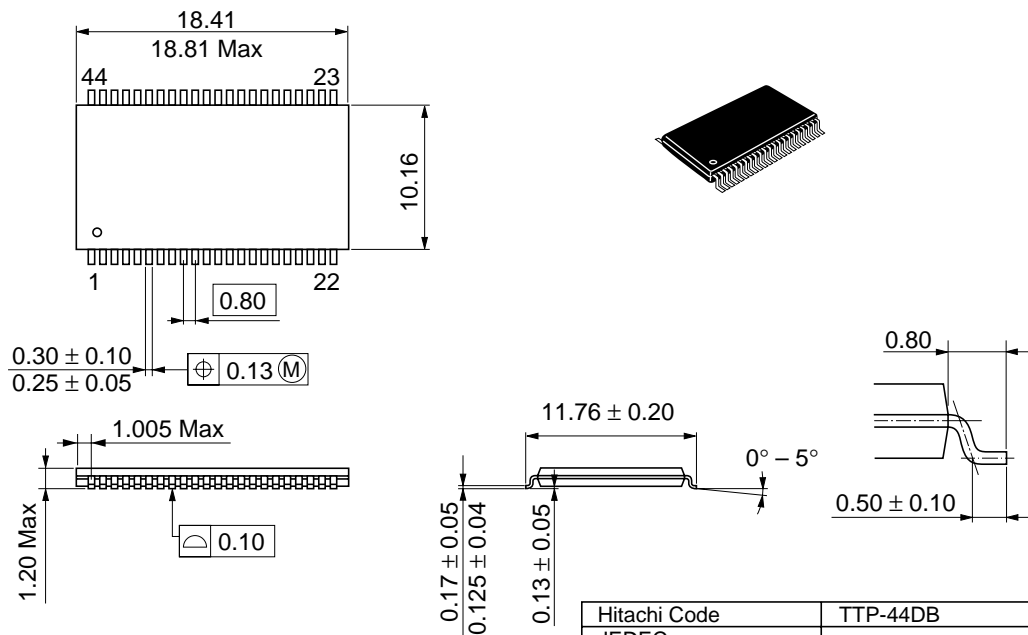
Low V_{CC} Data Retention Timing Waveform (2) (\overline{LB} , \overline{UB} Controlled)



Package Dimensions

HM62V16258BLTT Series (TTP-44DB)

Unit: mm



Dimension including the plating thickness
Base material dimension

Hitachi Code	TTP-44DB
JEDEC	—
EIAJ	—
Weight (reference value)	0.43 g

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